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RFM products are now Murata products.

RO3156E/E-1/E-2

868.950 MHz SAW Resonator



- Designed for European 868.95 MHz SRD Transmitters
- Very Low Series Resistance
- Quartz Stability
- Complies with Directive 2002/95/EC (RoHS)

The RO3156E is a true one-port, surface-acoustic-wave (SAW) resonator in a surface-mount ceramic case. It provides reliable, fundamental-mode, quartz frequency stabilization of fixed-frequency transmitters operating at 868.95 MHz. This SAW is designed specifically for SRD remote control and wireless security transmitters operating under ETSI EN 300 220.

Absolute Maximum Ratings

Rating	Value	Units
Input Power Level	0	dBm
DC Voltage	12	VDC
Storage Temperature	-40 to +125	°C
Operating Temperature Range	-40 to +125	°C
Soldering Temperature, 10 seconds / 5 cycles maximum	+260	°C

Electrical Characteristics

Characteristic		Sym	Notes	Minimum	Typical	Maximum	Units
Frequency, +25 °C	RO3156E			868.750		869.150	
	RO3156E-1	f_{C}		868.800		869.100	MHz
	RO3156E-2		2245	868.850		869.050	
Tolerance from 868.95 MHz	RO3156E		2,3,4,5			±200	kHz
	RO3156E-1	Δf_{C}				±150	
	RO3156E-2					±100	
Insertion Loss		IL	2,5,6		1.2	2.0	dB
Quality Factor	Unloaded Q	Q _U	5,6,7		6700		
	50 $Ω$ Loaded Q	Q _L			800		
Temperature Stability	Turnover Temperature	T _O	6,7,8	10	25	40	°C
	Turnover Frequency	f _O			f _C		kHz
	Frequency Temperature Coefficient	FTC	1		0.032		ppm/°C ²
Frequency Aging	Absolute Value during the First Year	fA	1		<±10		ppm/yr
DC Insulation Resistance between Any Two Terminals			5	1.0			MΩ
RF Equivalent RLC Model	Motional Resistance	R _M			14.1		Ω
	Motional Inductance	L_M	5, 6, 7, 9		17.2		μH
	Motional Capacitance	C_{M}			2.0		fF
	Shunt Static Capacitance	Co	5, 6, 9		2.3		pF
Test Fixture Shunt Inductance			2, 7		14.6		nΗ
Lid Symbolization (in addition to Lot and/or Date Codes)		L _{TEST} 2, 7 14.6 nH RO3156E: 707, RO3156E-1: 708, RO3156E-2: 926 // YWWS					
Standard Reel Quantity	Reel Size 7 Inch		10	5	00 Pieces / R	eel	
	Reel Size 13 Inch		10	30	000 Pieces / R	teel	



CAUTION: Electrostatic Sensitive Device. Observe precautions for handling. NOTES:

- Frequency aging is the change in f_C with time and is specified at +65 $^{\circ}C$ or less. Aging may exceed the specification for prolonged temperatures above +65 °C. Typically, aging is greatest the first year after manufacture, decreasing in subse-
- quent years.

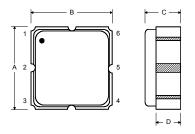
 The center frequency, f_C, is measured at the minimum insertion loss point, IL_{MIN},
- with the resonator in the 50 Ω test system (VSWR \leq 1.2:1). The shunt inductance, L_{TEST}, is tuned for parallel resonance with C_O at f_C. Typically, foscillator or fransmitter is approximately equal to the resonator fc.
- One or more of the following United States patents apply: 4,454,488 and 4.
- Typically, equipment utilizing this device requires emissions testing and government approval, which is the responsibility of the equipment manufacturer. Unless noted otherwise, case temperature $T_C = \pm 25 \pm 2$ °C.
- 5.
- The design, manufacturing process, and specifications of this device are subject

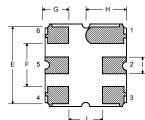
- Derived mathematically from one or more of the following directly measured parameters: f_C , IL, 3 dB bandwidth, f_C versus T_C , and C_O .
- Turnover temperature, T_O, is the temperature of maximum (or turnover) frequency, f_O. The nominal frequency at any case temperature, T_C, may be calculated from: $f = f_O [1 - FTC (T_O - T_C)^2]$. Typically oscillator T_O is approximately equal to the specified resonator To.
- This equivalent RLC model approximates resonator performance near the resonant frequency and is provided for reference only. The capacitance C_0 is the static (nonmotional) capacitance between the two terminals measured at low the statut (horhinouthar) capacitance between the two terminals measured at low frequency (10 MHz) with a capacitance meter. The measurement includes parasitic capacitance with "NC" pads unconnected. Case parasitic capacitance is approximately 0.05 pF. Transducer parallel capacitance can by calculated as: $C_P \approx C_O - 0.05$ pF.
- 10. Tape and Reel Standard for ANSI / EIA 481.

Electrical Connections

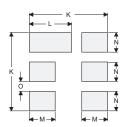
The SAW resonator is bidirectional and may be installed with either orientation. The two terminals are interchangeable and unnumbered. The callout NC indicates no internal connection. The NC pads assist with mechanical positioning and stability. External grounding of the NC pads is recommended to help reduce

Pin Connection		
1	NC	
2	Terminal	
3	NC	
4	NC	
5	Terminal	



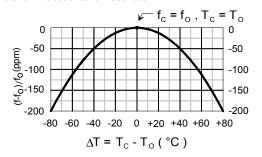






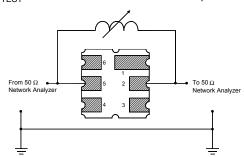
Temperature Characteristics

The curve shown accounts for resonator

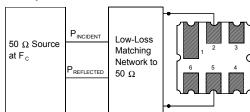


Characterization Test Circuit

Inductor L_{TEST} is tuned to resonate with the static capacitance, C_O, at F_C.



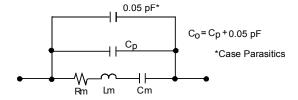
Power Dissipation Test



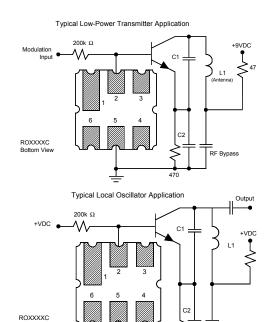
Case and Typical PCB Land Dimensions

Ref	mm			Inches		
	Min	Nom	Max	Min	Nom	Max
Α	2.87	3.00	3.13	0.113	0.118	0.123
В	2.87	3.00	3.13	0.113	0.118	0.123
С	1.12	1.25	1.38	0.044	0.049	0.054
D	0.77	0.90	1.03	0.030	0.035	0.040
E	2.67	2.80	2.93	0.105	0.110	0.115
F	1.47	1.60	1.73	0.058	0.063	0.068
G	0.72	0.85	0.98	0.028	0.033	0.038
Н	1.37	1.50	1.63	0.054	0.059	0.064
ı	0.47	0.60	0.73	0.019	0.024	0.029
J	1.17	1.30	1.43	0.046	0.051	0.056
K		3.20			0.126	
L		1.70			0.067	
М		1.05			0.041	
N		0.81			0.032	
0		0.38			0.015	

Equivalent RLC Model



Example Application Circuits



RF Bypass